


DXTP560BP5
**500V PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR
POWERDI®5**
Features and Benefits

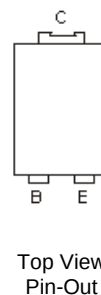
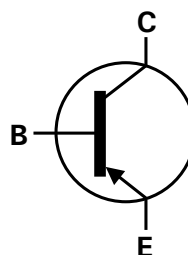
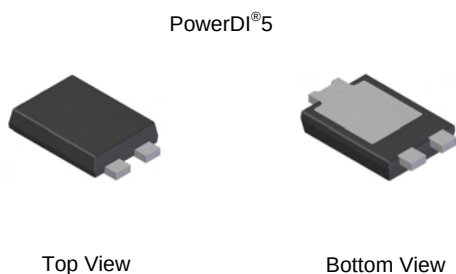
- $BV_{CEO} > -500V$
- $I_C = -150mA$ Continuous Collector Current
- 47% smaller than SOT223; 60% smaller than TO252 (D-PAK)
- Profile height just 1.1mm for thin application
- $R_{\theta JA}$ efficient giving high P_D rating up to 2.8W
- **"Lead Free", RoHS Compliant (Note 1)**
- **Halogen and Antimony Free, "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: POWERDI®5
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.093 grams (approximate)

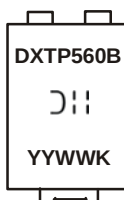
Applications

- Gate driver
- Startup switch in offline lighting
- Motor Control


Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXTP560BP5-13	DXTP560B	13	16	5,000

- Notes:
1. No purposefully added lead.
 2. Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>

Marking Information


DXTP560B = Product Type Marking Code
DII = Manufacturers' Code Marking
K = Factory Designator
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 10 for 2010)
WW = Week code (01 - 53)

Maximum Ratings @T_A = 25°C unless otherwise specified

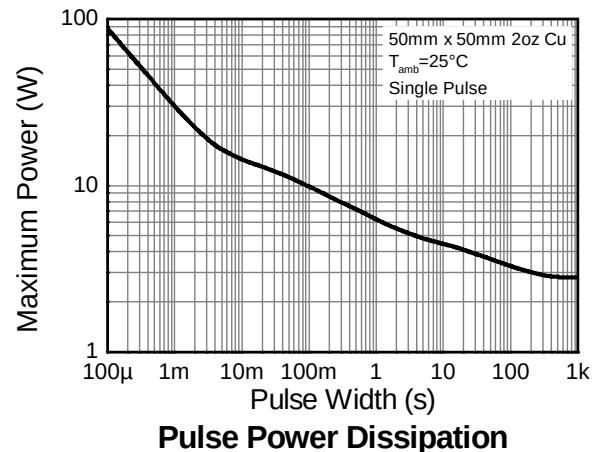
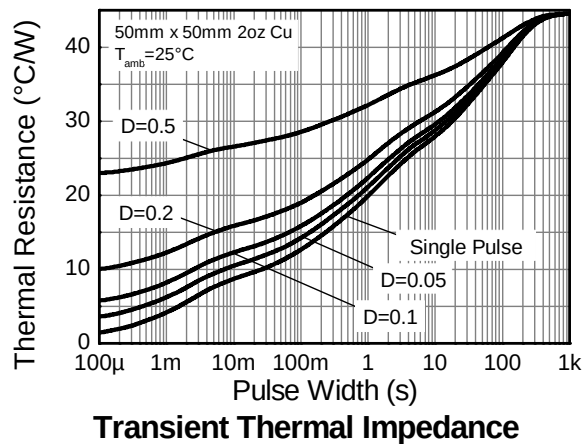
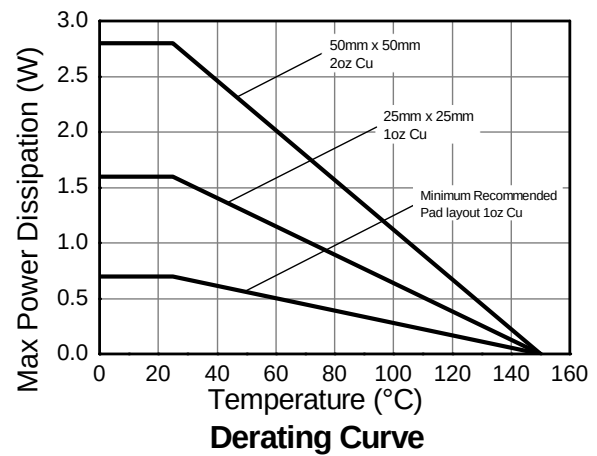
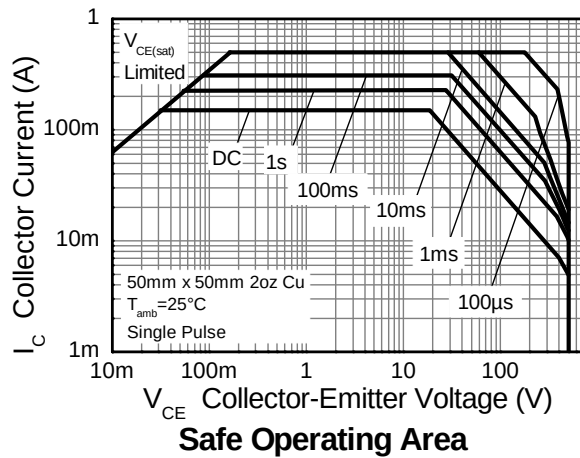
Characteristic		Symbol	Limit	Unit
Collector-Base Voltage		V _{CBO}	-500	V
Collector-Emitter Voltage		V _{CEO}	-500	
Emitter-Base Voltage		V _{EBO}	-7	
Continuous Collector Current	(Note 4)	I _C	-150	mA
Peak Pulse Current		I _{CM}	-500	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 4)	P _D	2.8	W mW/°C
			22.4	
	(Note 5)		1.3	
			10.4	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	0.7	°C/W
			5.6	
	(Note 4)		45	
	(Note 5)		96	
Thermal Resistance, Junction to Lead	(Note 6)	R _{θJL}	179	°C/W
	(Note 7)		14	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes:
4. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
 5. Same as note (4), except the device is mounted on 25mm x 25mm 1oz copper.
 6. Same as note (4), except the device is mounted on a minimum recommended pad layout of 1oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

Thermal Characteristics

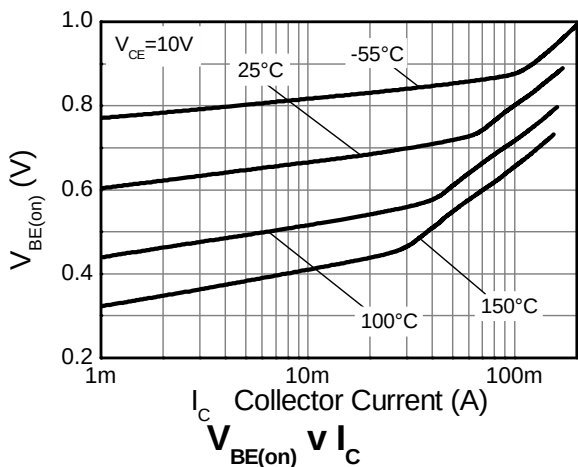
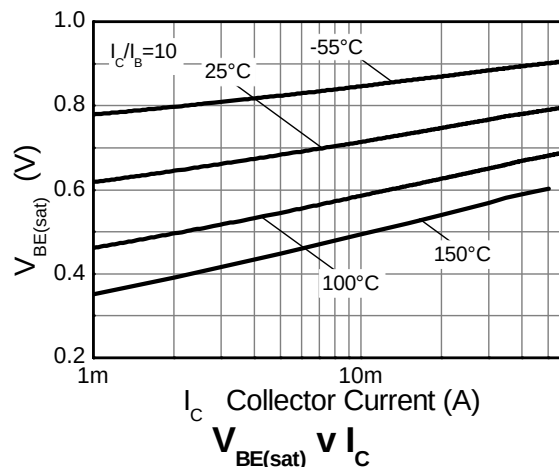
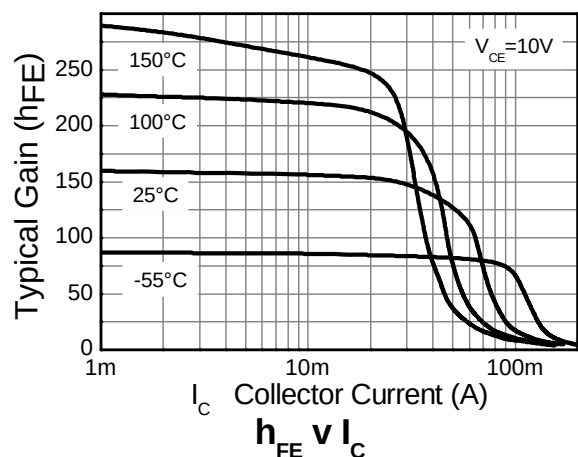
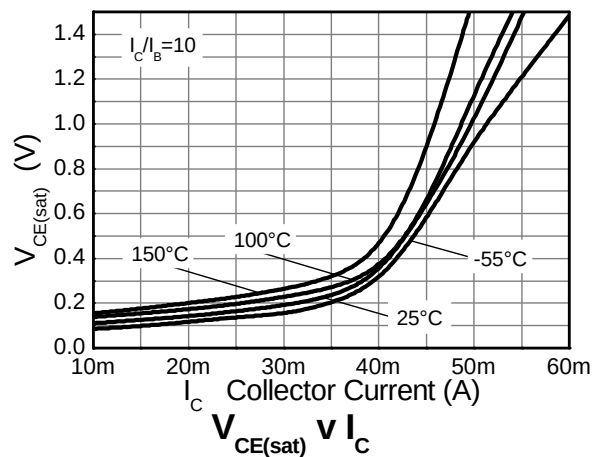
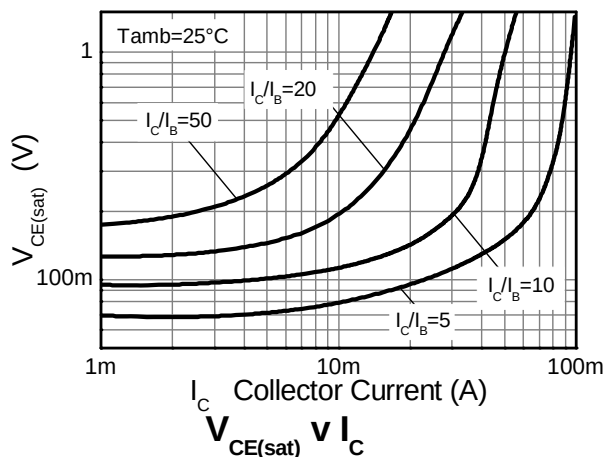


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-500	—	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-500	—	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	—	—	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	—	—	-100	nA	V _{CB} = -500V
Collector Cutoff Current	I _{CES}	—	—	-100	nA	V _{CE} = -500V
Emitter Cutoff Current	I _{EBO}	—	—	-100	nA	V _{EB} = -5.6V
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	—	—	-200 -500	mV	I _C = -20mA, I _B = -2mA I _C = -50mA, I _B = -10mA
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}	—	—	-900	mV	I _C = -50mA, I _B = -10mA
Base-Emitter Turn-On Voltage (Note 8)	V _{BE(on)}	—	—	-900	mV	V _{CE} = -10V, I _C = -50mA
DC Current Gain (Note 8)	h _{FE}	100 80 —	— — 15	300 300 —	—	V _{CE} = -10V, I _C = -1mA V _{CE} = -10V, I _C = -50mA V _{CE} = -10V, I _C = -100mA
Transition Frequency	f _T	60	—	—	MHz	V _{CE} = -20V, I _C = -10mA, f = 50MHz
Output Capacitance	C _{obo}	—	—	8	pF	V _{CB} = -20V, f = 1MHz
Switching Times	t _{on} t _{off}	— —	110 1500	— —	ns	V _{CC} = -100V, I _C = -50mA, I _{B1} = 5mA, I _{B2} = -10mA

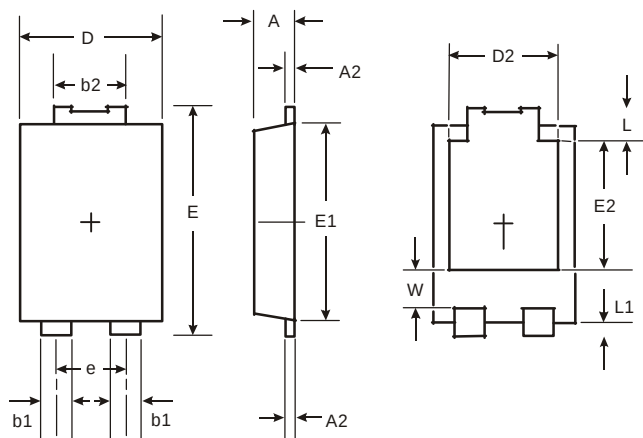
Notes: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics



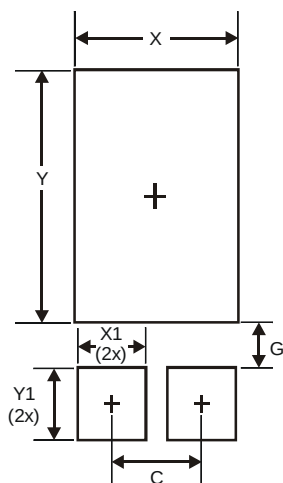
DXTP560BP5

Package Outline Dimensions



POWERDI [®] 5		
Dim	Min	Max
A	1.05	1.15
A2	0.33	0.43
b1	0.80	0.99
b2	1.70	1.88
D	3.90	4.05
D2	3.054 Typ	
E	6.40	6.60
e	1.84 Typ	
E1	5.30	5.45
E2	3.549 Typ	
L	0.75	0.95
L1	0.50	0.65
W	1.10	1.41
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
C	1.840
G	0.852
X	3.360
X1	1.390
Y	4.860
Y1	1.400

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